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Data Sheet

LED Display Chip

EODC-660-19-02

Rev. 03, 2017

Radiation	Type	Electrodes
Red	GaAsP/GaAs, diffusion type	p (anode) up

<p>All sizes in μm</p>	<p>Application:</p> <p>This miniature device is an excellent choice for applications where small size and reduced space are important factors such as complex displays in optical devices for laboratory, measurement, control- and medical equipment</p> <hr/> <p>Typ dimensions:</p> <p>typ thickness: 290 μm cathode: Au-alloy metalization anode: Al metalization</p>
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Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Cond.*	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 5 \text{ mA}$		1.75	2	V
Reverse voltage	V_R	$I_R = 10 \mu\text{A}$	5			V
Luminous intensity/segment**	I_V	$I_F = 5 \text{ mA}$	55	80		μcd
I_V ratio segment to segment**		$I_F = 5 \text{ mA}$			1.75	
I_V ratio to adjacent chip		$I_F = 5 \text{ mA}$			2	
Peak wavelength	λ_p	$I_F = 5 \text{ mA}$	650	660	670	nm
Spectral bandwidth at 50%	$\Delta\lambda_{0.5}$	$I_F = 5 \text{ mA}$		17		nm

*Current for one segment

**Measured on bare chip on TO-18 header

Miscellaneous Parameters

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Temperature coefficient of λ_C	$T_a = -40 \dots +120^\circ\text{C}$	$TC(\lambda_C)$	0.15	nm/K
Operating temperature range		T_{amb}	-40 to +120	$^\circ\text{C}$
Storage temperature range		T_{stg}	-40 to +125	$^\circ\text{C}$

Art. No. 115 005

Packing

Dice on adhesive film with wire-bond on top



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.